



B-24314-C2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

JOSEPH T. EVANS, JR. ET AL.

Serial No.:

582,672

Filed:

September 14, 1990

Group:

233

For:

NON-VOLATILE MEMORY CIRCUIT USING  
FERROELECTRIC CAPACITOR STORAGE ELEMENT

Honorable Commissioner of  
Patents and Trademarks  
Washington, D.C. 20231

Dear Sir:

SECOND PRELIMINARY AMENDMENT AND REQUEST  
FOR DECLARATION OF INTERFERENCE UNDER RULE 1.607

Please amend the above-referenced application as follows:

IN THE CLAIMS

Please add the following claims:

472. In a nonvolatile ferroelectric memory of the type having a plurality of memory cells, a bit line coupled to each said memory cell, each said memory cell comprising a ferroelectric capacitor having first and second plate electrodes, the polarization of said capacitors corresponding to the data stored therewithin, the improvement wherein:

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:  
Commissioner of Patents and Trademarks,

Washington, D.C. 20231 on October 10, 1990  
(Date of Deposit)

Roger N. Chauza, Reg. No. 29,753

Name of applicant, assignee, or  
Registered Representative

[Signature]  
Signature

October 10, 1990  
Date of Signature